#### UNIVERSITY OF SWAZILAND

#### **FACULTY OF SCIENCE**

#### **DEPARTMENT OF PHYSICS**

**MAIN EXAMINATION:** 

**DECEMBER 2007** 

TITLE OF PAPER : ELECTRONICS I

COURSE NUMBER :

P311

TIME ALLOWED

**THREE HOURS** 

**INSTRUCTIONS**:

ANSWER ANY FOUR OUT OF FIVE QUESTIONS

**EACH QUESTION CARRIES 25 MARKS** 

MARKS FOR DIFFERENT SECTIONS ARE SHOWN

IN THE RIGHT-HAND MARGIN.

THIS PAPER HAS 8 PAGES, INCLUDING THIS PAGE.

DO NOT OPEN THE PAPER UNTIL PERMISSION HAS BEEN GIVEN BY THE INVIGILATOR.

- (a) With the aid of examples, explain the meaning of the following terms:
  - (i) majority carriers;

(2 marks)

(ii) minority carriers.

(2 marks)

(b) A low-power diode has the current-voltage characteristic given by the figures in the table below.

Forward voltage (V)	0	0.7	0.8	0.9	1.0	1.1	1.2	1.3	1.4
Forward current (mA)	0	1	5	28	65	120	175	240	330

The diode is connected in the circuit shown in Fig. 1.1.

(i) Draw the I-V characteristics of the diode;

(4 marks)

(ii) Determine the current flowing in the diode;

(2 marks)

(iii) Calculate the value of the load resister  $R_L$ 

(2 marks)

(iv) Calculate the power dissipated in both the diode and the load resistor;

(4 marks)

- (c) A Zener diode regulator circuit is to provide a 24 V supply to a variable load. The input voltage is 30 V and a 24 V, 400 mW Zener diode is to be used. Calculate:
  - (i) the series resistance  $R_1$  required and

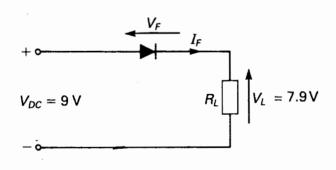
(4 marks)

(ii) the diode current when the load resistance is 2000  $\Omega$ .

(3 marks)

100 µA

(d) Fig. 1.2 shows the output characteristics of a transistor. Is the device n-p-n or p-n-p? Give reasons for your answer. (2 marks)



80 µA 60 µA 40 µA 20 µA

 $= 120 \mu A$ 

Fig. 1.1

Fig. 1.2 Collector-emitter voltage  $V_{CE}$  (V)

(a) Draw the block diagram of an n-p-n transistor with its base-emitter junction forward biased and its collector-base junction reverse biased. Mark on the diagram the directions of the base current, the electrons in the collector region, and the holes in the emitter region.

(3 marks)

- (b) In Fig. 2.1,  $V_{CC} = 12 \text{ V}$ ,  $I_C = 2\text{mA}$  and  $V_{BE} = 0.65 \text{ V}$ .
  - (i) Calculate  $R_3$  when 1/10th of the supply voltage appears across  $R_3$ ; (2 marks)
  - (ii) Calculate  $R_L$ , when  $V_{CE} = V_{CC}/2$ ; (2 marks)
  - (iii) Calculate  $I_B$  when  $h_{FE} = 100$  (2 marks)
  - (iv) Calculate  $R_2$  when  $I_{R2} = 10I_B$  (4 marks)
- (c) Draw the load line for a d.c. load of 400  $\Omega$  on the output characteristics given in Fig. 2.2. The operating point is at  $I_B = 150 \,\mu\text{A}$  and the supply voltage is 20 V. (Note: Use the enlarged version of Fig. 2.2 given on page 7to draw the loadline).

(3 marks)

- (ii) Calculate  $V_E$ ,  $V_{CE}$  and collector-to-earth voltage when the emitter resistance is 100  $\Omega$ . (4 marks)
- (iii) Determine the peak-to-peak output voltage when a sinusoidal voltage varies the base current by  $\pm$  50  $\mu$ A. (5 marks)

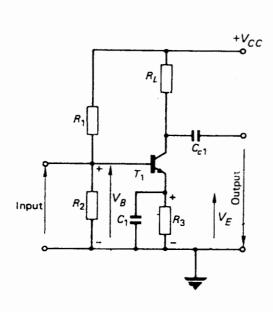


Fig. 2.1

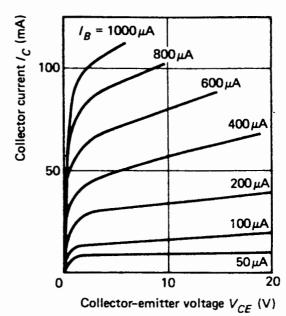


Fig. 2.2

- (a) With the aid of a diagram, describe the principle of operation of an n-channel JFET.

  (8 marks)
- (b) The drain-source voltage of a JFET is increased from 6 V to 7 V. The resulting increase in the drain current is 0.1 mA. Calculate the output resistance of the FET. Assume that there is zero change in the value of the gate-source voltage. (3 marks)
- (c) Figure 3.1 shows both the mutual and drain characteristics of an n-channel JFET.
  - (i) Assuming that  $V_{DD}=20$  V, draw the load line for  $R_L=2000$   $\Omega$  on the drain characteristics and select the operating point  $V_{GS}=-2$  V. (Note: Use the enlarged version of Fig. 3.1 given on page 8 to draw the loadline). (4 marks)
  - (ii) Determine from the drain characteristics the mutual conductance of the device when  $V_{GS}$  varies between the limits -1V and -3 V; (4 marks)
  - (iii) Calculate the voltage gain from the load line; (4 marks)
  - (iv) Calculate the theoretical voltage gain of a common source amplifier build using the JFET represented by the characteristics shown in Fig. 3.1. (2 marks)

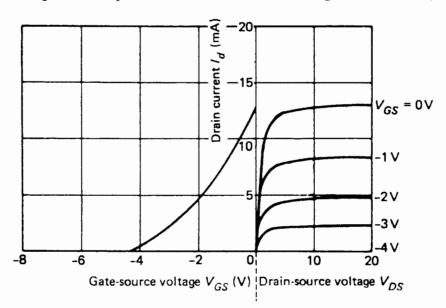
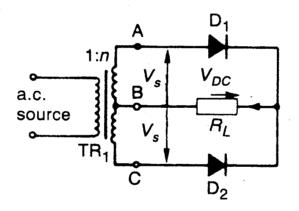


Fig. 3.1

- (a) Explain, briefly, why a p-n junction diode acts as a rectifier. (2 marks)
- (b) How does the reverse saturation current of a p-n junction diode vary with temperature? (4 marks)
- (c) The input transformer of a full-wave rectifier (Fig. 4.1) has a turns ratio of 9.58:1. The r.m.s. voltage at the secondary is 24 V. Calculate:
  - (i) the r.m.s. input voltage; (4 marks)
  - (ii) the peak current flowing in the 200  $\Omega$  load; (3 marks)
  - (iii) the d.c. current in the 200  $\Omega$  load. (4 marks)
- (d) A Zener diode stabilising circuit has an input voltage of 18 V and a diode current of 8 mA to give 10 V across the load of 1200  $\Omega$ . Calculate
  - (i) the value of the series resistor; (4 marks)
  - (ii) the diode current when the load resistance is  $1000 \Omega$ . (4 marks)



Assume that  $D_1$  and  $D_2$  represent silicon diodes.

Fig. 4.1

(a) What is meant by hybrid parameters?

(3 marks)

- (b) Consider a bipolar junction transistor with the following h-parameters:  $h_{oe} = 6 \times 10^{-5} \text{S}$ ,  $h_{ie} = 1.2 \text{ k}\Omega$ , and  $h_{fe} = 150$ . The transistor is used to build an amplifier with a collector resistance of 2 k $\Omega$ .
  - (i) Draw a detailed equivalent circuit of this amplifier and label it; (4 marks)
  - (ii) Calculate the voltage gain of the amplifier when  $h_{ce}$  is neglected; (3 marks)
  - (iii) Calculate the voltage gain when  $h_{\infty}$  is taken into account. (4 marks)
- (c) The application of a signal voltage of 7.5 mV peak between the base and emitter terminals of an n-p-n transistor causes the emitter current to vary by  $\pm$  0.5 mA about its d.c. value.
  - (i) Calculate the a.c. voltage developed across a 1.2 k $\Omega$  collector resistor when the common-base current gain,  $\alpha = 0.99$ ; (3 marks)
  - (ii) Calculate the voltage gain of the circuit.

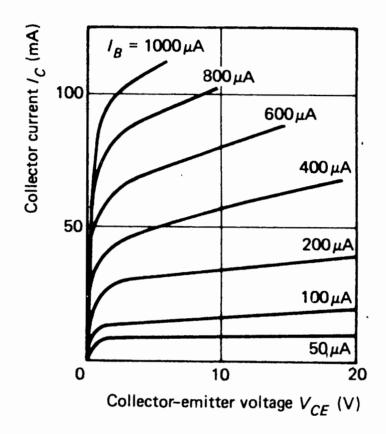
(2 marks)

- (d) An audio-frequency amplifier uses a FET with  $r_{ds} = 10 \text{ k}\Omega$  and  $g_m = 5 \text{ ms}$ . What value of drain load resistor is needed to give a voltage gain of -40? (3 marks)
- (e) Explain what is wrong with the following statement. An n-p-n transistor is operated with its base-emitterjunction forward biased and its collector-base junction reverse biased. When the base potential is made more negative, the collector current is reduced in value.

(3 marks)

## **USE THE GRAPH BELOW TO ANSWER QUESTION 2 (c)(i)**

(An enlarged version of Fig. 2.2)

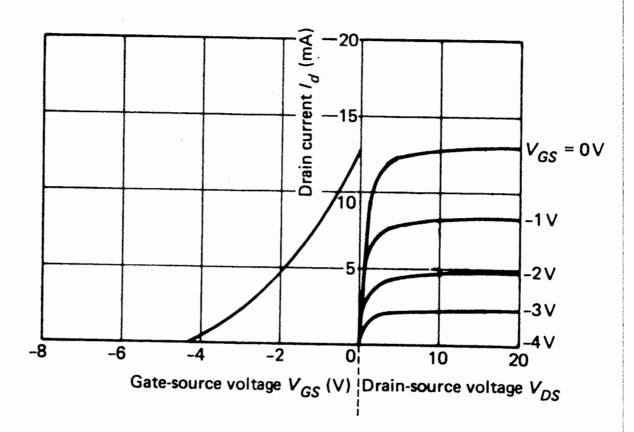


NOTE: This graph should be handed in together with the answer book.

## CANDIDATE'S EXAMINATION NUMBER.....

# USE THE GRAPH BELOW TO ANSWER QUESTION 3 (c)(i)

(An enlarged version of Fig. 3.1)



NOTE: This graph should be handed in together with the answer book.